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Silicon NPN Power Transistors BU2525DF

DESCRIPTION

·With TO-3PFa package
·High voltage
·High speed switching
·Built-in damper diode

APPLICATIONS

·For use in horizontal deflection circuits of large screen colour TV receivers

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter

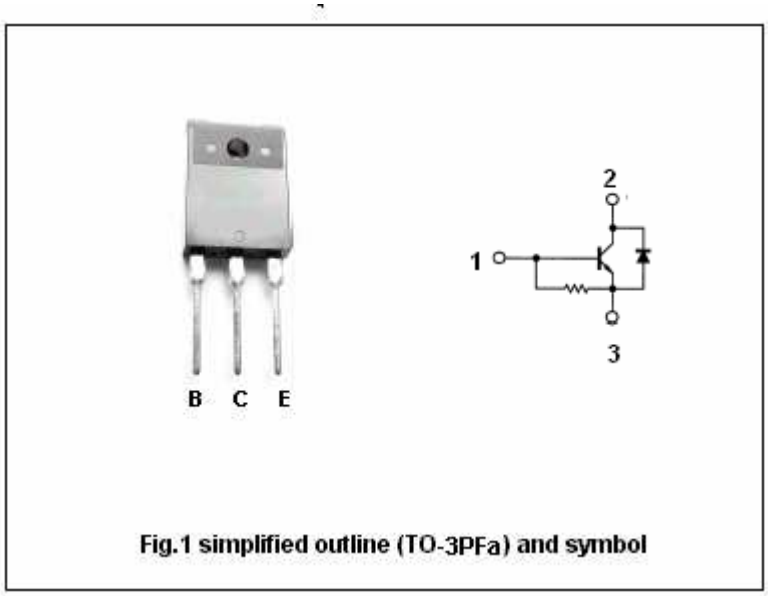


Fig.1 simplified outline (TO-3PFa) and symbol

Absolute maximum ratings(Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	800	V
V_{EBO}	Emitter-base voltage	Open collector	7.5	A
I_C	Collector current (DC)		12	A
I_{CM}	Collector current -peak		30	A
I_B	Base Collector current (DC)		8	A
I_{BM}	Base current -peak		12	A
P_{tot}	Total power dissipation	T_C=25□	45	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-65~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEO(SUS)}$	Collector-emitter sustaining voltage	I_C=100mA ;I_B=0,L=25mH	800			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=600mA ;I_C=0	7.5	13.5		V
V_{CEsat}	Collector-emitter saturation voltage	I_C=8A ;I_B=1.6 A			5.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=8A ;I_B=1.6 A			1.1	V
I_{CES}	Collector cut-off current	V_{CE}=$BV_{CES;}$ V_{BE}=0 T_j=125□			1.0 2.0	mA
I_{EBO}	Emitter cut-off current	V_{EB}=6V; I_C=0	72	110	218	mA
h_{FE-1}	DC current gain	I_C=1.0A ; V_{CE}=5V		11		
h_{FE-2}	DC current gain	I_C=8A ; V_{CE}=5V	5	7	9.5	
V_F	Diode forward voltage	I_F=8A		1.6	2.0	V
C_C	Collector capacitance	I_E=0, f=1MHz;V_{CB}=10V		145		pF

PACKAGE OUTLINE

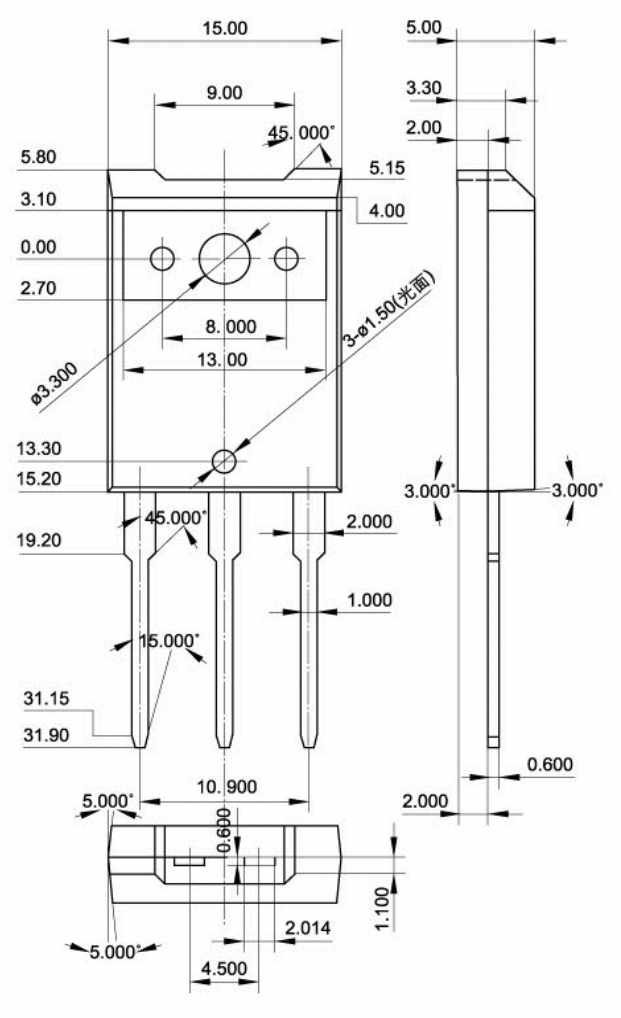


Fig.2 Outline dimensions (unindicated tolerance:±0.30mm)